

Customer No.: 31561
Application No.: 10/709,924
Docket No.: 13366-US-PA

REMARKS

This is a full and timely response to the outstanding nonfinal Office Action mailed May 24, 2006. Reconsideration and allowance of the pending claims 1, 2, 4-6 and 15-18 are respectfully requested.

Discussion of Office Action Rejections

The Office Action rejected claims 1, 2, 4-6 and 15-18 under 35 U.S.C. 102(b) as being anticipated by Yang US Patent 6,306,700 (hereinafter Yang).

In response to the rejection to claims 1, 2, 4-6 and 15-18 under 35 U.S.C. 102(b) as being anticipated by Yang, Applicant respectfully traverses this rejection.

Applicant submits that the high-voltage metal-oxide-semiconductor devices as set forth in claims 1, 2, 4-6 and 15-18 are neither taught, disclosed, nor suggested by Yang or any of the other cited references, taken alone or in combination.

Specifically, at least two features of claim 1 are neither taught, disclosed, nor suggested by Yang. The drift region (such as the drift region 260 shown in Fig. 2B) of claim 1 is connected with the channel region (such as the channel region 230 shown in Fig. 2B) and the at least one doped region (such as the doped regions 240/250 shown in Fig. 2B), but the drift region 216 of Yang is not connected to at least one of the of doped regions 232a/b. Moreover, the drift region (such as the drift region 260 shown in Fig. 2B) of claim 1 and the modifying doped region (such as the modifying doped region 270 shown in Fig. 2B) together completely surround the

Customer No.: 31561
Application No.: 10/709,924
Docket No.: 13366-US-PA

doped regions (such as the doped regions 240/250 shown in Fig. 2B), but the doped regions 232a/b of Yang are merely surround by the modifying doped regions 222a/b.

Meanwhile, at least two features of claim 5 are neither taught, disclosed, nor suggested by Yang. The drift region (such as the drift region 260 shown in Fig. 2B) of claim 5 is connected with the channel region (such as the channel region 230 shown in Fig. 2B) and the at least one doped region (such as the doped regions 240/250 shown in Fig. 2B), but the drift region 216 of Yang is not connected to at least one of the of doped regions 232a/b. Moreover, the doped region 240/250 of claim 5 includes the lightly doped grade region (such as the grade extension region 262 Fig. 2B), but the doped regions 232a/b of Yang do not.

Furthermore, at least one features of claim 6 is neither taught, disclosed, nor suggested by Yang. The drift region (such as the drift region 260 shown in Fig. 2B) of claim 6 is connected with the channel region (such as the channel region 230 shown in Fig. 2B) and the at least one doped region (such as the doped regions 240/250 shown in Fig. 2B), but the drift region 216 of Yang is not connected to at least one of the of doped regions 232a/b.

Accordingly, the present invention as set forth in claims 1, 5 and 6 should not be considered as being anticipated by Yang, and claims 1, 5 and 6 should be allowable. For at least the same reasons, dependent claims 2, 4 and 15-18 patently define over the prior art as a matter of law, for at least the reason that these dependent claims contain all features of their respective independent claim.

Customer No.: 31561
Application No.: 10/709,924
Docket No.: 13366-US-PA

CONCLUSION

For at least the foregoing reasons, it is believed that the pending claims 1, 2, 4-6 and 15-18 are in proper condition for allowance and an action to such effect is earnestly solicited. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

Date : *July 19, 2006*

Respectfully submitted,



Ding Yu Tan

Registration No.: 58,812

Jianq Chyun Intellectual Property Office
7th Floor-1, No. 100
Roosevelt Road, Section 2
Taipei, 100
Taiwan
Tel: 011-886-2-2369-2800
Fax: 011-886-2-2369-7233
Email: belinda@jcipgroup.com.tw;
usa@jcipgroup.com.tw